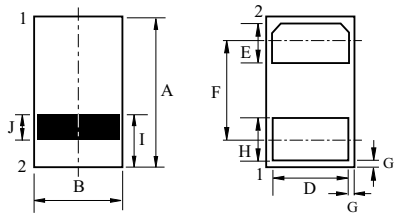
KDV142EL

SILICON EPITAXIAL PIN TYPE DIODE

For antenna switches in mobile applications.

FEATURES

- Low Capacitance : C_T=0.35[pF] (Max.)
- Low Series resistance : r_S=1.3[Ω] (Max.)
- Small Package .



DIM	MILLIMETERS
A	0.6 ± 0.05
B	0.3 ± 0.05
C	0.28 ± 0.05
D	0.25 ± 0.05
E	0.18 ± 0.05
F	Typ 0.36
G	0.025 ± 0.02
H	0.2 ± 0.05
I	Max 0.3
J	Typ 0.1

ELP-2

MAXIMUM RATING (Ta=25℃)

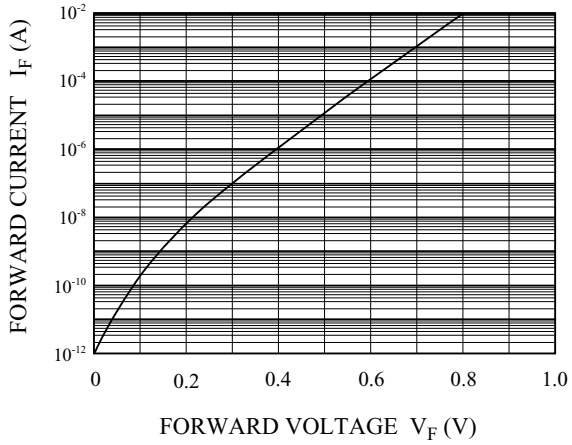
CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	30	V
Forward Current	I_F	100	mA
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

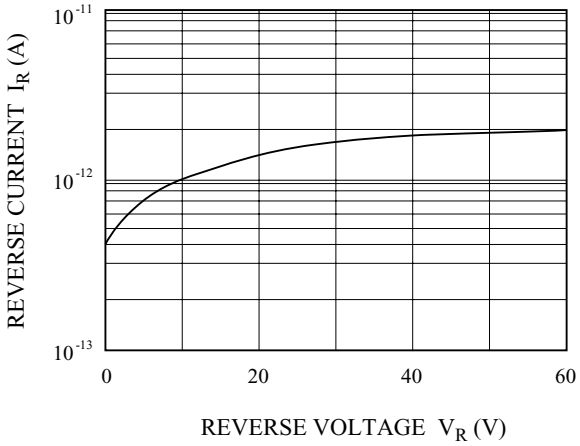
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Current	I_R	V_R=30V	-	-	0.1	μA
Forward Voltage	V_F	I_F=10mA	-	-	1.0	V
Total Capacitance	C_T	V_R=1V, f=1MHz	-	-	0.35	pF
Series Resistance	r_s	I_F=10mA, f=100MHz	-	-	1.3	Ω
ESD-Capability *	-	C=200pF, R=0 Ω, Both forward and reverse direction 1 pulse	100	-	-	V

* Failure cirterion : I_R>100nA at V_R=30V.

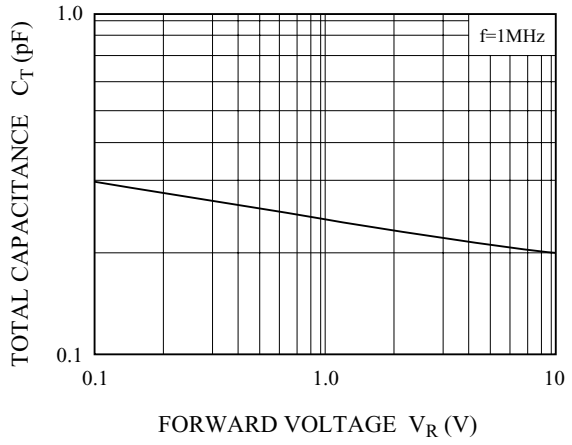
I_F - V_F



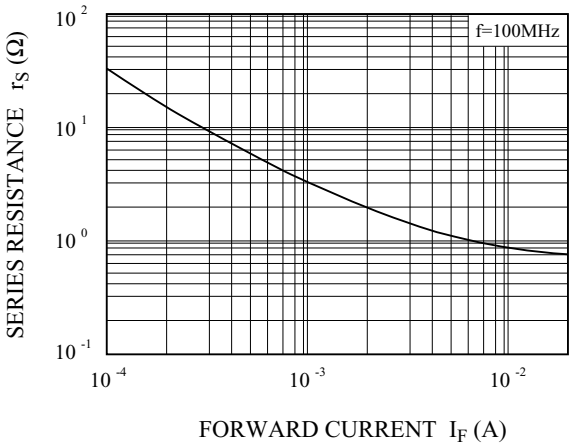
I_R - V_R



C_T - V_R



r_S - I_F



r_P - V_F

